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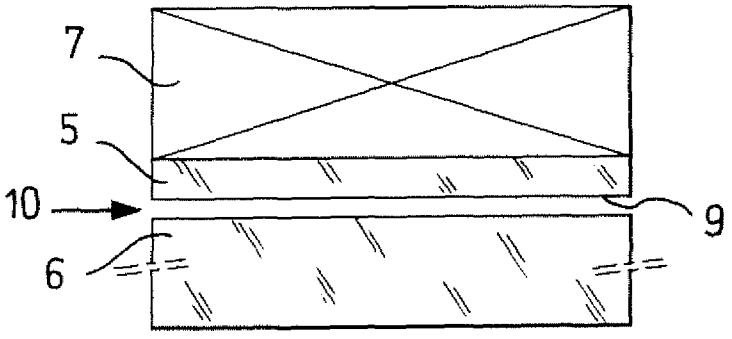
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(54) **Title:** PROCESS FOR SIMPLIFICATION OF A FINISHING SEQUENCE AND STRUCTURE OBTAINED BY THE PROCESS



(57) **Abstract:** According to a first aspect, this invention concerns a process for the formation of a structure comprising a thin layer (8) made of a semi conducting material on a substrate (7), including steps to create a weakened zone 5 (3) within the thickness of a donor substrate (1), to bring the donor substrate (1) into intimate contact with a support substrate(7), to detach the donor substrate (1) at the weakened zone (3) to transfer part (5) of the donor substrate (1) onto the support substrate (7), to 10 treat the said part (5) of the donor substrate transferred onto the support substrate to form the said thin layer (8), the said treatment consisting of a sequence of finishing operations; the process being characterised in that: 15 - detachment is achieved by the application of a heat treatment to develop weakening of the weakened zone (3), without initiating thermal detachment of the said part of the donor substrate; and application of an energy pulse (10) provoking self-maintained detachment of the 20 said part (5) of the donor substrate; - and in that the sequence of finishing operations is a sequence simplified by eliminating the first or the last operation of a sequence consisting of repeating the sequencing of a smoothing operation of the free surface 25 (9) of the said part (5) of the donor substrate transferred onto the support substrate, with a thinning operation of the said part (5) of the donor substrate transferred onto the support substrate.

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